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2813

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>AB</i>	AA	5,972,800	10/99	Hasegawa			
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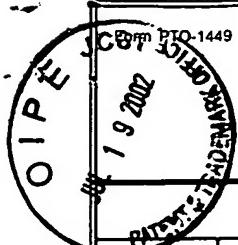
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<i>SL</i>	AR		Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies", IEEE 1998, pp. 589-592.				
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*hansen Scilley*

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<i>AM</i>	AR	Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.
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